

Table 1. Material parameters used for the IPCE analysis with references in bracket. n/p-type, is a material doped negatively or positively, E_{gap} , is the bandgap, V_{FB} , is the flatband potential, N , is the doping concentration, ϵ_r , is the relative permittivity, V_{IPCE} , is the applied potential at which the IPCE was measured, and d , is the thickness of the material. The first value of each parameter is the nominal value and the second or third values are estimated variations.

Material	n/p-type	E_{gap} (eV)	V_{FB} (VRHE)	N (cm^{-3})	ϵ_r (-)	V_{IPCE} (VRHE)	d (nm)	Measurements of reflection	Wavelength's range (nm)
Cu ₂ O	p	2.0	1.05 or 0.73	7.1×10^{13}	7.5	0	50 μm	No	500-700
Si	p	1.12	0.20 or 0.13	2.5×10^{17}	11.7	-1	500 μm	Yes	600-1000
Fe ₂ O ₃	n	2.0	0.34	4.0×10^{18}	32	1.46	25	No	300-700
Fe ₂ O ₃	n	2.0	0.54	2.6×10^{18}	32	1.46	25	No	300-700
BiVO ₄	n	2.5	0.08 or 0.1	5×10^{17} $10^{18}-10^{17}$	68	1	~200	No	320-575
Cu ₂ V ₈ O ₃	n	2.0	~0.5	10^{19} $10^{20}-10^{18}$	20	1.5	283	No	320-575
CuFeO ₂	p	1.55	1.01	10^{18}	20	0.4	290	Yes	350-850
nano-Fe ₂ O ₃	n	2.0	0.54	2.5×10^{18} $10^{19}-10^{18}$	32	1.23	~500	No	350-702
nano- Fe ₂ O ₃ -CoB _i	n	2.0	0.54	2.5×10^{18} $10^{19}-10^{18}$	32	1.23	~500	No	350-702
LaTiO ₂ N	n	2.1	0.1	7.4×10^{17}	15	1.23	1420	Yes	420-710